2SD1823

Silicon NPN epitaxial planar type

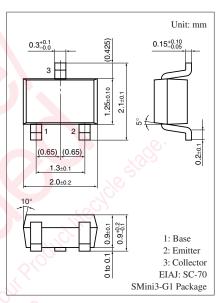
For low-frequency amplification

Features

- High forward current transfer ratio h_{FE}
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- High emitter-base voltage (Collector open) V_{EBO}
- Low noise voltage NV
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Parameter	Symbol	Rating	Unit				
Collector-base voltage (Emitter open)	V _{CBO}	50	v				
Collector-emitter voltage (Base open)	V _{CEO}	40	V				
Emitter-base voltage (Collector open)	V _{EBO}	15	V				
Collector current	I _C	50	mA				
Peak collector current	I _{CP}	100	mA				
Collector power dissipation	P _C	150	mW				
Junction temperature	Tj	150	°C				
Storage temperature	T _{stg}	-55 to +150	°C				





Marking symbol: 1Z

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

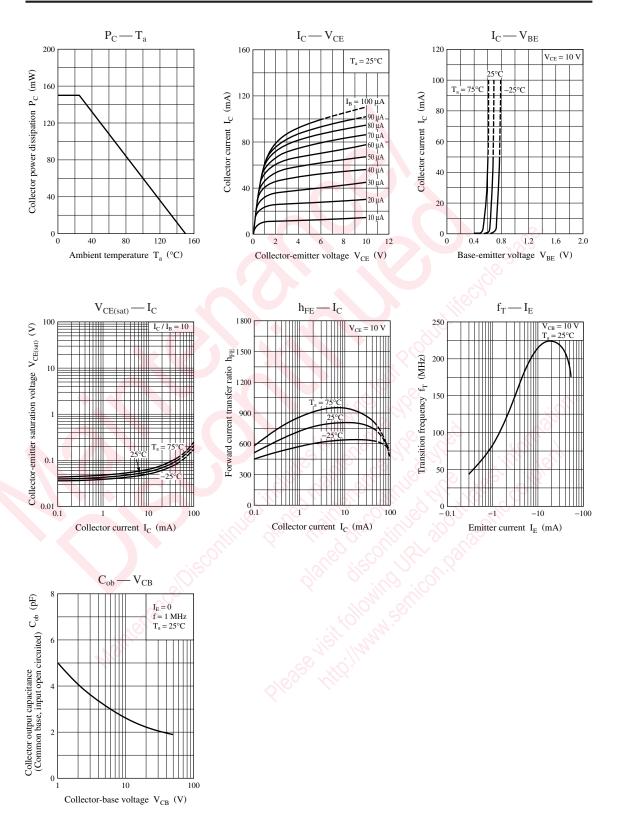
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$	40			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	15			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 20 \text{ V}, I_B = 0$			1	μΑ
Forward current transfer ratio *	h _{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	400		2 0 0 0	—
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$		0.05	0.20	V
Transition frequency	f _T	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		120		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	R	S	Т
$h_{\rm FE}$	400 to 800	600 to 1 200	1000 to 2000

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